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# TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT

(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.  
YOR920030203US1

In Re Application Of: Stephen W. Bedell, et al.

(16694)

AUG 15 2005

Application No.	Filing Date	Examiner	Customer No.	Group Art Unit	Confirmation No.
10/662,028	September 12, 2003	Unknown	23389	3661	9297

Title: **FORMULATION OF A SILICON GERMANIUM-ON-INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER**

Address to:

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

## 37 CFR 1.97(b)

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

## 37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

☐ the statement specified in 37 CFR 1.97(e);

OR

☐ the fee set forth in 37 CFR 1.17(p).

**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**  
(Under 37 CFR 1.97(b) or 1.97(c))

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Title: **FORMULATION OF A SILICON GERMANIUM-ON-INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER**

**Payment of Fee**

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

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- ☒ The Director is hereby authorized to charge and credit Deposit Account No. **50-0510/IBM** as described below.
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**Leslie S. Szivos**

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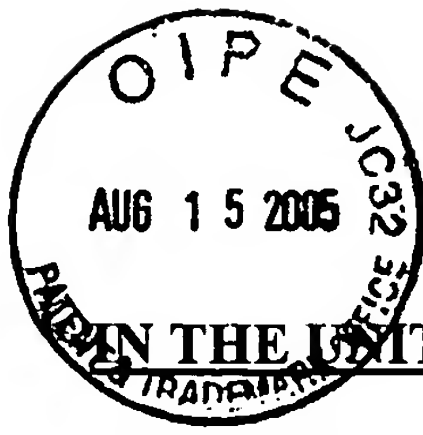
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Dated: **August 12, 2005**

**Leslie S. Szivos**  
**Registration No. 39,394**

**SCULLY, SCOTT, MURPHY & PRESSER**  
**400 Garden City Plaza, Suite 300**  
**Garden City, New York 11530**  
**(516) 742-4343**

CC:



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**Applicants:** Stephen W. Bedell, et al.

**Examiner:** Unknown

**Serial No.:** 10/662,028

**Art Unit:** 3661

**Filed:** September 12, 2003

**Docket:** YOR920030203US1 (16694)

**For:** FORMULATION OF A SILICON  
GERMANIUM-ON-INSULATOR  
STRUCTURE BY OXIDATION OF A  
BURIED POROUS SILICON LAYER

**Date:** August 12, 2005

**Confirmation No:** 9297

Mailstop Amendment  
Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Sir:

In accordance with 37 C.F.R §§1.97 and 1.98, it is requested that the following references, which are also listed on the attached Form PTO-1449, be made of record in the above-identified case.

1. U.S. Patent No. 4,104,090, issued August 1, 1978, to Pogge, et al.;
2. U.S. Patent No. 5,686,343, issued November 11, 1997, to Lee, et al.;

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**CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)**

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on August 12, 2005.

Dated: August 12, 2005

  
\_\_\_\_\_  
Leslie S. Szivos

3. Mizuno, et al., "High Performance CMOS Operation of Strained-SOI MOSFETs Using Thin Film SiGe-On-Insulator Substrate", 2002 Symposium on VLSI Technology, Digest of Technical Papers, Honolulu, June 11-13, 2002, Symposium on VLSI Technology, New York, NY: IEEE, US, June 11, 2002, pp. 106-107, XP001109839;

4. Patent Abstracts of Japan, Vol. 005, No. 181 (E-083), November 20, 1981; and

5. Patent Abstracts of Japan, Vol. 005, No. 117 (E-067), May 18, 1981.

The references were cited in an International Search Report dated May 17, 2005 received from the European Patent Office. Applicants are submitting copies of references 3-5, together with a copy of the International Search Report. The relevance of each the above-identified references has been described in the Search Report as defining the general state of the art.

In the event an Action on the merits crosses in the mail, the applicants state the following:

"That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement."

Inasmuch as this Information Disclosure Statement is being submitted in accordance with the schedule set out in 37 C.F.R. § 1.97(b), no statement or fee is required.

Respectfully submitted,

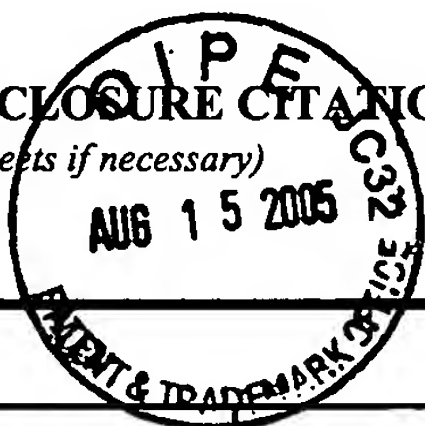


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(516) 742-4343

LSS:gc

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>	Docket Number (Optional) <b>YOR920030203US1 (16694)</b>	Application Number <b>10/662,028</b>
	Applicant(s) <b>Stephen W. Bedell, et al.</b>	
	Filing Date <b>September 12, 2003</b>	Group Art Unit <b>3661</b>



U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		4,104,090	08/01/1978	Pogge, et al.			
		5,686,343	11/11/1997	Lee, et al.			

U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS			<i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>
		Mizuno, et al., "High Performance CMOS Operation of Strained-SOI MOSFETs Using Thin Film SiGe-On-Insulator Substrate", 2002 Symposium on VLSI Technology, Digest of Technical Papers, Honolulu, June 11-13, 2002, Symposium on VLSI Technology, New York, NY: IEEE, US, June 11, 2002, pp. 106-107, XP001109839	
		Patent Abstracts of Japan, Vol. 005, No. 181 (E-083), November 20, 1981	

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
		Patent Abstracts of Japan, Vol. 005, No. 117 (E-067), May 18, 1981						
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